

1 Ω On Resistance, ±15 V/+12 V/±5 V *i*CMOS SPST Switches

ADG1401/ADG1402

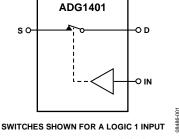
FEATURES

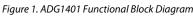
1 Ω on resistance 0.2 Ω on resistance flatness Up to 430 mA continuous current Fully specified at +12 V, ±15 V, ±5 V No V_L supply required 3 V logic-compatible inputs Rail-to-rail operation 8-lead MSOP and 8-lead, 3 mm × 2 mm LFCSP packages

APPLICATIONS

Automatic test equipment Data acquisition systems Battery-powered systems Sample-and-hold systems Audio signal routing Video signal routing Communication systems Relay replacements

FUNCTIONAL BLOCK DIAGRAM





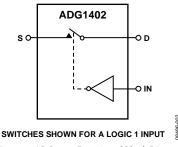


Figure 2. ADG1402 Functional Block Diagram

GENERAL DESCRIPTION

The ADG1401/ADG1402 contain a single-pole/single-throw (SPST) switch. Figure 1 shows that with a logic input of 1, the switch of the ADG1401 is closed and that of the ADG1402 is open. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked.

The *i*CMOS^{*} (industrial CMOS) modular manufacturing process combines high voltage, complementary metal-oxide semiconductor (CMOS) and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no other generation of high voltage parts has achieved. Unlike analog ICs using conventional CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and a reduced package size. The on resistance profile is very flat over the full analog input range ensuring excellent linearity and low distortion when switching audio signals. The *i*CMOS construction ensures ultralow power dissipation, making the part ideally suited for portable and battery-powered instruments.

PRODUCT HIGHLIGHTS

- 1. 1.3 Ω maximum on resistance at 25°C.
- 2. Minimum distortion.
- 3. 3 V logic-compatible digital inputs: $V_{INH} = 2.0 \text{ V}, V_{INL} = 0.8 \text{ V}.$
- 4. No V_L logic power supply required.
- 5. 8-lead MSOP and 8-lead, $3 \text{ mm} \times 2 \text{ mm}$ LFCSP packages.

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REVISION HISTORY

10/09—Revision 0: Initial Version

SPECIFICATIONS ±15 V DUAL SUPPLY

 V_{DD} = +15 V \pm 10%, V_{SS} = -15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, Ron	1			Ωtyp	$V_s = \pm 10 \text{ V}$, $I_s = -10 \text{ mA}$; see Figure 20
	1.3	1.6	1.8	Ωmax	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
On Resistance Flatness, R _{FLAT (ON)}	0.2			Ωtyp	$V_s = \pm 10 V$; $I_s = -10 mA$
	0.23	0.26	0.3	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +16.5 \text{ V}, \text{V}_{SS} = -16.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_{s} = \pm 10 V$, $V_{D} = \pm 10 V$; see Figure 21
	±0.4	±3	±150	nA max	_
Drain Off Leakage, I _D (Off)	±0.05			nA typ	$V_{s} = \pm 10 V$, $V_{D} = \pm 10 V$; see Figure 21
-	±0.4	±3	±150	nA max	
Channel On Leakage, I _D , I _s (On)	±0.2			nA typ	$V_s = V_D = \pm 10 V$; see Figure 22
2	±1	±3	±150	nA max	_
DIGITAL INPUTS	1				
Input High Voltage, VINH			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, linL or linH	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	4			pF typ	
DYNAMIC CHARACTERISTICS ¹	-			1	
t _{on}	120			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
-ON	150	185	215	ns max	$V_s = 10 V;$ see Figure 23
t _{OFF}	120	105	215	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
COFF	150	175	200	ns max	$V_s = 10 V_s$ see Figure 23
Charge Injection	-12	175	200	pC typ	$V_s = 0.0$, $S_c = 0.0$, $C_L = 1$ nF; see Figure 24
Off Isolation	-58			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
Total Harmonic Distortion + Noise	0.008			% typ	$R_L = 10 k\Omega$, 5 V rms, f = 20 Hz to 20 kHz;
	0.000			70 typ	see Figure 27
–3 dB Bandwidth	120			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
Insertion Loss	0.08			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 26
Cs (Off)	36			pF typ	$f = 1 MHz$, $V_s = 0 V$
C _D (Off)	41			pF typ	$f = 1 MHz$, $V_s = 0 V$
C _D , C _s (On)	187			pF typ	$f = 1 MHz, V_s = 0 V$
POWER REQUIREMENTS					$V_{DD} = +16.5 V, V_{SS} = -16.5 V$
l _{DD}	0.002			μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
			1.0	μA max	
lod	60			μA typ	Digital inputs = 5 V
			95	μA max	
lss	0.002			μA typ	Digital inputs = 0 V, 5 V, or V_{DD}
			1.0	μA max	
V _{DD} /V _{SS}			±4.5/±16.5	V min/max	Ground = 0 V

+12 V SINGLE SUPPLY

 V_{DD} = +12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{\text{DD}}$	V	
On Resistance, R _{on}	2			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$; see Figure 20
	2.4	2.9	3.2	Ωmax	$V_{DD} = 10.8 V, V_{SS} = 0 V$
On Resistance Flatness, R _{FLAT (ON)}	0.6			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$
	0.68	0.8	0.85	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 13.2 V, V_{SS} = 0 V$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_{s} = 1 V/10 V$, $V_{D} = 10 V/1 V$; see Figure 21
-	±0.4	±3	±150	nA max	
Drain Off Leakage, I _D (Off)	±0.05			nA typ	$V_{s} = 1 V/10 V$, $V_{D} = 10 V/1 V$; see Figure 21
3 • • •	±0.4	±3	±150	nA max	
Channel On Leakage, I _D , I _S (On)	±0.2			nA typ	$V_s = V_D = 1 V$ or 10 V; see Figure 22
9 • • • •	±1	±3	±150	nA max	
DIGITAL INPUTS					
Input High Voltage, VINH			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, Inc or Inh	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	4			pF typ	
				F: 7F	
ton	180			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	235	295	335	ns max	$V_s = 8 V$; see Figure 23
toff	140			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	185	215	260	ns max	$V_s = 8 V$; see Figure 23
Charge Injection	57	2.0	200	pC typ	$V_s = 6 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 24
Off Isolation	-58			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
–3 dB Bandwidth	82			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
Insertion Loss	0.15			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 26
C _s (Off)	61			pF typ	$f = 1 \text{ MHz}, V_s = 6 \text{ V}$
$C_{\rm D}$ (Off)	68			pF typ	$f = 1 \text{ MHz}, V_S = 6 \text{ V}$
C_D, C_S (On)	181			pF typ	$f = 1 \text{ MHz}, V_S = 6 \text{ V}$
POWER REQUIREMENTS	101				$V_{DD} = 13.2 V$
	0.001			μA typ	Digital inputs = $0 \text{ V or } V_{DD}$
עטי	0.001		1.0	μΑ typ μΑ max	
DD	60		1.0	μA typ	Digital inputs = 5 V
יישו	00		95	μΑ typ μΑ max	
Ver			95 5/16.5		$Ground = 0 V, V_{SS} = 0 V$
V _{DD}			5/10.5	V min/max	$divultu = v v, v_{SS} = v v$

±5 V DUAL SUPPLY

 V_{DD} = +5 V \pm 10%, V_{SS} = -5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{\text{DD}}$	V	
On Resistance, R _{ON}	2.3			Ωtyp	$V_s = \pm 4.5 \text{ V}, I_s = -10 \text{ mA}; \text{ see Figure 20}$
	2.7	3.3	3.7	Ωmax	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On Resistance Flatness, R _{FLAT (ON)}	0.65			Ωtyp	$V_{s} = \pm 4.5 V$, $I_{s} = -10 mA$
	0.72	0.85	0.9	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.02			nA typ	$V_s = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V};$ see Figure 21
	±0.4	±3	±150	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	
	±0.4	1.2	+150		$V_{\text{S}}=\pm4.5$ V, $V_{\text{D}}=\mp4.5$ V; see Figure 21
Channel On Leakage L. L. (On)	±0.4 ±0.1	±3	±150	nA max	$V_{s} = V_{D} = \pm 4.5 V$; see Figure 22
Channel On Leakage, I _D , I _S (On)	±0.1 ±1	±3	±150	nA typ nA max	$v_S = v_D = \pm 4.3 v$, see Figure 22
	ΞI	ΞЭ	±130	na max	
DIGITAL INPUTS			2.0	Vmin	
Input High Voltage, V _{INH}			2.0		
Input Low Voltage, VINL	0.000		0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002		10.1	µA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
Digital lagest Conseiton as	4		±0.1	μA max	
Digital Input Capacitance, C _{IN} DYNAMIC CHARACTERISTICS ¹	4			pF typ	
	200				
t _{on}	290	160	520	ns typ	$R_{L} = 300 \Omega, C_{L} = 35 \text{ pF}$
	375	460	520	ns max	$V_{s} = 3 V$; see Figure 23
t _{off}	235	265	405	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$ V ₅ = 3 V; see Figure 23
Chause Injection	305	365	405	ns max	$V_s = 3 V$; see Figure 23 $V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 24
Charge Injection	145			pC typ	
Off Isolation	-58			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
Total Harmonic Distortion + Noise	0.02			% typ	R_L = 10 kΩ, 5 V p-p, f = 20 Hz to 20 kHz; see Figure 27
–3 dB Bandwidth	79			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
Insertion Loss	0.14			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 26
Cs (Off)	52			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D (Off)	58			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D , C _s (On)	198			pF typ	$V_{s} = 0 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = +5.5 V, V_{SS} = -5.5 V$
ldd	0.001			μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
			1.0	μA max	
lss	0.001			μA typ	Digital inputs = $0 V$ or V_{DD}
			1.0	µA max	
V _{DD} /V _{SS}			±4.5/±16.5	V min/max	Ground = 0 V

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 4.

Parameter	25°C	85°C	125°C	Unit	Test Conditions/Comments
CONTINUOUS CURRENT, S or D ¹					
±15 V Dual Supply					$V_{DD} = +13.5 V, V_{SS} = -13.5 V$
8-Lead MSOP ($\theta_{JA} = 206^{\circ}C/W$)	275	190	125	mA maximum	
8-Lead LFCSP ($\theta_{JA} = 50.8^{\circ}C/W$)	430	275	160	mA maximum	
+12 V Single Supply					$V_{DD} = 10.8 V, V_{SS} = 0 V$
8-Lead MSOP ($\theta_{JA} = 206^{\circ}C/W$)	255	180	120	mA maximum	
8-Lead LFCSP ($\theta_{JA} = 50.8^{\circ}C/W$)	355	235	145	mA maximum	
±5 V Dual Supply					$V_{DD} = +4.5 V, V_{SS} = -4.5 V$
8-Lead MSOP ($\theta_{JA} = 206^{\circ}C/W$)	250	175	120	mA maximum	
8-Lead LFCSP ($\theta_{JA} = 50.8^{\circ}C/W$)	340	225	140	mA maximum	

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 5.

ParameterRatingVDD to Vss35 VVDD to GND-0.3 V to +25 VVss to GND+0.3 V to -25 VAnalog Inputs1Vss - 0.3 V to VDD + 0.3 V or 30 mA, whichever occurs firstDigital Inputs1GND - 0.3 V to VDD + 0.3 V or 30 mA, whichever occurs firstPeak Current, S or D (Pulsed at 1 ms, 10%) Duty-Cycle Maximum)500 mA8-Lead MSOP (4-Layer Board)500 mA8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature150°CReflow Soldering Peak Temperature, Pb Free260°C	1 ubic 5.	
Void NoContinueVoid No-0.3 V to +25 VVoid No+0.3 V to -25 VAnalog Inputs1Vss - 0.3 V to Void Void Void Void Void Void Void Voi	Parameter	Rating
Vss to GND+0.3 V to -25 VAnalog Inputs1Vss - 0.3 V to VDD + 0.3 V or 30 mA, whichever occurs firstDigital Inputs1GND - 0.3 V to VDD + 0.3 V or 30 mA, whichever occurs firstPeak Current, S or D (Pulsed at 1 ms, 10% Duty-Cycle Maximum) 8-Lead MSOP (4-Layer Board) 8-Lead LFCSP500 mA 700 mAContinuous Current per Channel, S or D500 mA 700 mAOperating Temperature Range Industrial-40°C to +125°C -65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	V _{DD} to V _{SS}	35 V
Analog Inputs1 $V_{ss} - 0.3 V$ to $V_{DD} + 0.3 V$ or 30 mA, whichever occurs firstDigital Inputs1GND - 0.3 V to $V_{DD} + 0.3 V$ or 30 mA, whichever occurs firstPeak Current, S or D (Pulsed at 1 ms, 10% Duty-Cycle Maximum) 8-Lead MSOP (4-Layer Board) 8-Lead LFCSP500 mA8-Lead MSOP (4-Layer Board) 8-Lead LFCSP500 mAContinuous Current per Channel, S or D700 mAOperating Temperature Range Industrial -40° C to $+125^{\circ}$ CStorage Temperature Range Junction Temperature -40° C to $+150^{\circ}$ CSubstriation Temperature Reflow Soldering Peak 260° C	V _{DD} to GND	–0.3 V to +25 V
30 mA, whichever occurs firstDigital Inputs1GND - 0.3 V to V_DD + 0.3 V or 30 mA, whichever occurs firstPeak Current, S or D (Pulsed at 1 ms, 10% Duty-Cycle Maximum)500 mA8-Lead MSOP (4-Layer Board)500 mA8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature150°CSelfow Soldering Peak260°C	Vss to GND	+0.3 V to -25 V
30 mA, whichever occurs firstPeak Current, S or D (Pulsed at 1 ms, 10%) Duty-Cycle Maximum) &-Lead MSOP (4-Layer Board)500 mA8-Lead MSOP (4-Layer Board) 8-Lead LFCSP500 mAContinuous Current per Channel, S or D700 mAOperating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	Analog Inputs ¹	
(Pulsed at 1 ms, 10% Duty-Cycle Maximum)500 mA8-Lead MSOP (4-Layer Board)500 mA8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	Digital Inputs ¹	
Duty-Cycle Maximum)8-Lead MSOP (4-Layer Board)500 mA8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	Peak Current, S or D	
8-Lead MSOP (4-Layer Board)500 mA8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C		
8-Lead LFCSP700 mAContinuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	Duty-Cycle Maximum)	
Continuous Current per Channel, S or DData in Table 4 + 15%Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature Reflow Soldering Peak260°C	8-Lead MSOP (4-Layer Board)	500 mA
Channel, S or D-40°C to +125°CIndustrial-40°C to +125°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CReflow Soldering Peak260°C	8-Lead LFCSP	700 mA
Operating Temperature Range Industrial-40°C to +125°CStorage Temperature Range Junction Temperature-65°C to +150°CStorage Temperature150°CReflow Soldering Peak260°C	Continuous Current per	Data in Table 4 + 15%
Industrial -40° C to $+125^{\circ}$ CStorage Temperature Range -65° C to $+150^{\circ}$ CJunction Temperature 150° CReflow Soldering Peak 260° C	Channel, S or D	
Storage Temperature Range-65°C to +150°CJunction Temperature150°CReflow Soldering Peak260°C	Operating Temperature Range	
Junction Temperature150°CReflow Soldering Peak260°C	Industrial	–40°C to +125°C
Reflow Soldering Peak 260°C	Storage Temperature Range	–65°C to +150°C
	Junction Temperature	150°C
Temperature, Pb Free	Reflow Soldering Peak	260°C
	Temperature, Pb Free	

¹ Over voltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

Table 6. Thermal Resistance

Package Type	θιΑ	οıθ	Unit
8-Lead MSOP (4-Layer Board)	206	44	°C/W
8-Lead LFCSP	50.8		°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Figure 3. ADG1401/ADG1402 Pin Configuration

Table 7. ADG1401/ADG1402 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	S	Source Terminal. This pin can be an input or output.
2	NC	No Connect.
3	GND	Ground (0 V) Reference.
4	V _{DD}	Most Positive Power Supply Potential.
5	NC	No Connect.
6	IN	Logic Control Input.
7	Vss	Most Negative Power Supply Potential.
8	D	Drain Terminal. This pin can be an input or output.
	EPAD	Exposed pad tied to substrate, V _{SS} , for LFCSP package.

Table 8. ADG1401/ADG1402 Truth Table

ADG1401 IN	ADG1402 IN	Switch Condition
1	0	On
0	1	Off

TYPICAL PERFORMANCE CHARACTERISTICS

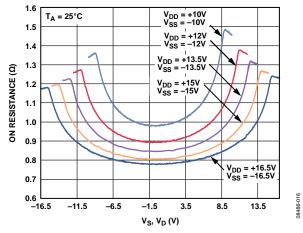


Figure 4. On Resistance as a Function of V_D (V_S) for Dual Supply

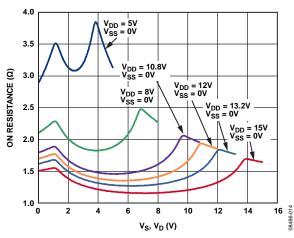


Figure 5. On Resistance as a Function of V_D (V_s) for Single Supply

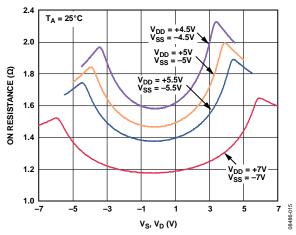


Figure 6. On Resistance as a Function of V_D (V_S) for Dual Supply

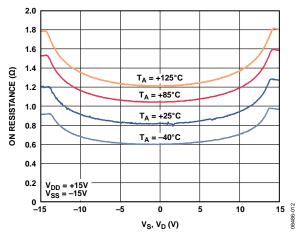


Figure 7. On Resistance as a Function of V_D (V₃) for Different Temperatures, ± 15 V Dual Supply

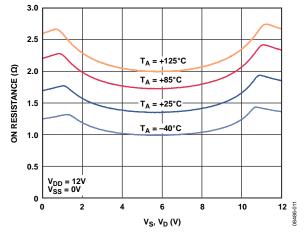


Figure 8. On Resistance as a Function of V_D (V_s) for Different Temperatures, +12 V Single Supply

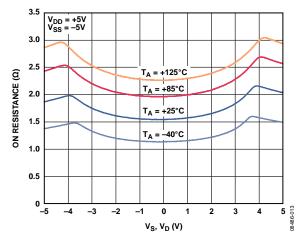
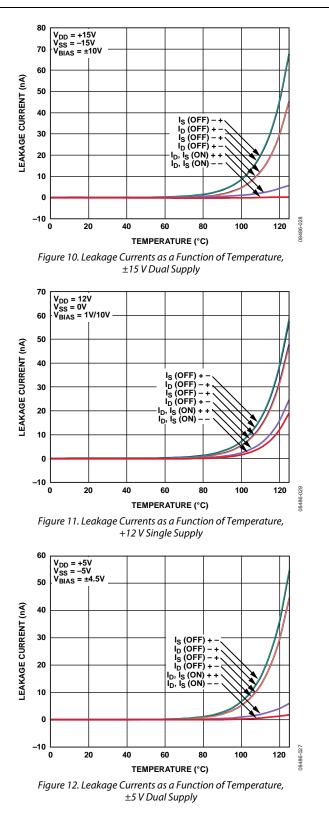
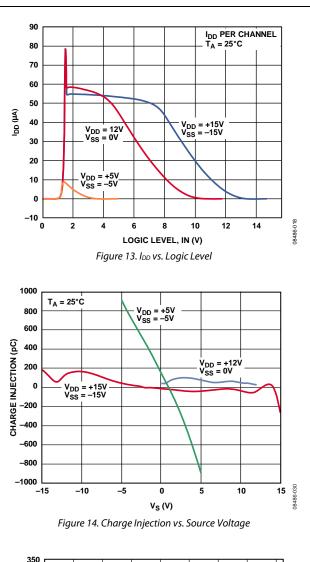
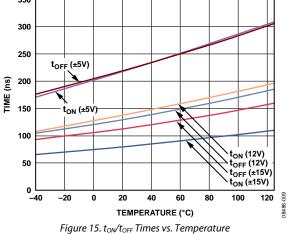


Figure 9. On Resistance as a Function of V_D (V_S) for Different Temperatures, ± 5 V Dual Supply







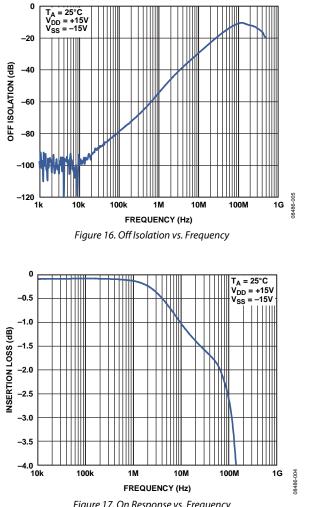
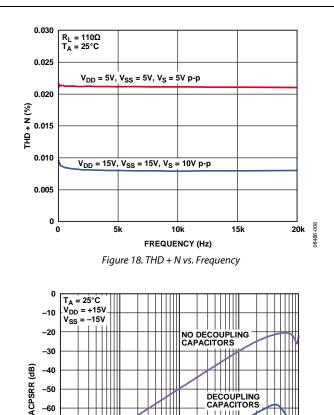


Figure 17. On Response vs. Frequency



100k

FREQUENCY (Hz)

Figure 19. ACPSRR vs. Frequency

08486-006 MDL

1M

-60

-70

-80

-90

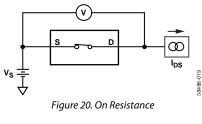
-100

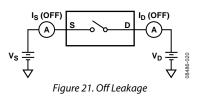
ĺk

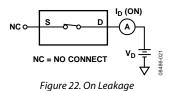
 \mathcal{H}

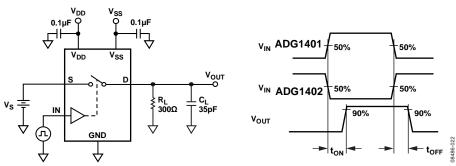
10k

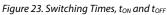
TEST CIRCUITS











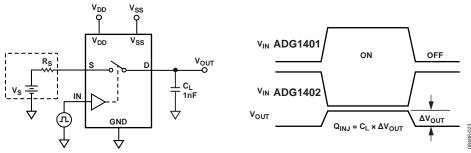
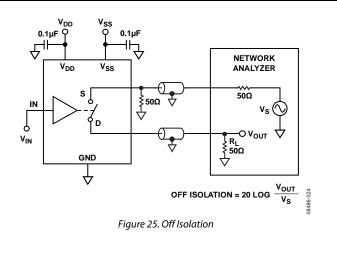


Figure 24. Charge Injection



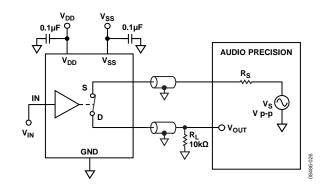


Figure 27. THD + N

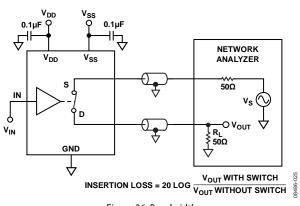


Figure 26. Bandwidth

TERMINOLOGY

Idd

The positive supply current.

Iss

The negative supply current.

$V_D(V_s)$

The analog voltage on Terminal D and Terminal S.

Ron

The ohmic resistance between Terminal D and Terminal S.

R_{FLAT} (ON)

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (Off)

The source leakage current with the switch off.

 \mathbf{I}_{D} (Off) The drain leakage current with the switch off.

 $I_{\rm D}, I_{\rm S}\left(On\right)$ The channel leakage current with the switch on.

VINL

The maximum input voltage for Logic 0.

 $V_{\mbox{\scriptsize INH}}$ The minimum input voltage for Logic 1.

$$\begin{split} I_{\text{INL}}\left(I_{\text{INH}}\right) \\ \text{The input current of the digital input.} \end{split}$$

Cs (Off)

The off switch source capacitance, measured with reference to ground.

C_D (Off)

The off switch drain capacitance, measured with reference to ground.

C_D , C_S (On)

The on switch capacitance, measured with reference to ground.

CIN

The digital input capacitance.

ton

Delay time between the 50% and 90% points of the digital input and switch on condition. See Figure 23.

toff

Delay time between the 50% and 90% points of the digital input and switch off condition. See Figure 23.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching. See Figure 24.

Off Isolation

A measure of unwanted signal coupling through an off switch. See Figure 25.

Bandwidth

The frequency at which the output is attenuated by 3 dB. See Figure 26.

On Response The frequency response of the on switch.

Insertion Loss The loss due to the on resistance of the switch. See Figure 26.

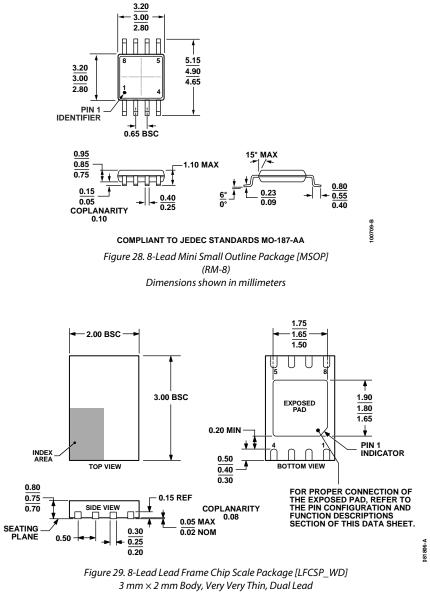
THD + N

The ratio of the harmonic amplitude plus noise of the signal to the fundamental. See Figure 27.

AC Power Supply Rejection Ratio (ACPSRR)

ACPSRR measures the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of the signal on the output to the amplitude of the modulation is the ACPSRR. See Figure 19.

OUTLINE DIMENSIONS



(CP-8-4)

Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG1401BRMZ ¹	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S2T
ADG1401BRMZ-REEL71	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S2T
ADG1401BCPZ-REEL71	-40°C to +125°C	8-Lead Lead Frame Chip Scale Package [LFCSP_WD]	CP-8-4	2Y
ADG1402BRMZ ¹	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S2U
ADG1402BRMZ-REEL71	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S2U
ADG1402BCPZ-REEL71	-40°C to +125°C	8-Lead Lead Frame Chip Scale Package [LFCSP_WD]	CP-8-4	1F

¹ Z = RoHS Compliant Part.

NOTES

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